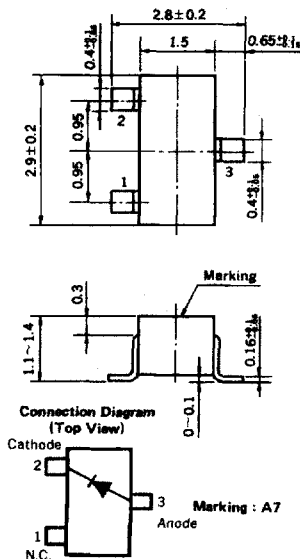


SILICON SWITCHING DIODES

1SS222, 1SS223

HIGH SPEED SWITCHING SILICON EPITAXIAL DIODES MINI MOLD

PACKAGE DIMENSIONS in millimeters



FEATURES

- Low capacitance: $C_t = 4.0$ pF MAX.
- High speed switching: $t_{rr} = 3.0$ ns MAX.
- Wide applications including switching, limiter, clipper.

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents ($T_a = 25^\circ\text{C}$)

		1SS222	1SS223	
Peak Reverse Voltage	V_{RM}	70	100	V
DC Reverse Voltage	V_R	70	100	V
Peak Forward Current	I_{FM}	300	300	mA
Average Rectified Current	I_O	100	100	mA
DC Forward Current	I_F	100	100	mA
Maximum Temperatures				
Junction Temperature	T_j	150		$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150		$^\circ\text{C}$
Thermal Resistance				
Junction to Ambient	$R_{th(j-a)}$	0.67		$^\circ\text{C}/\text{mW}$

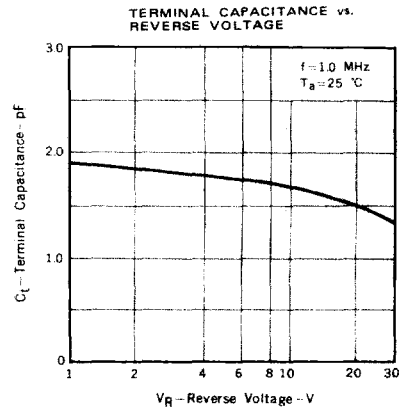
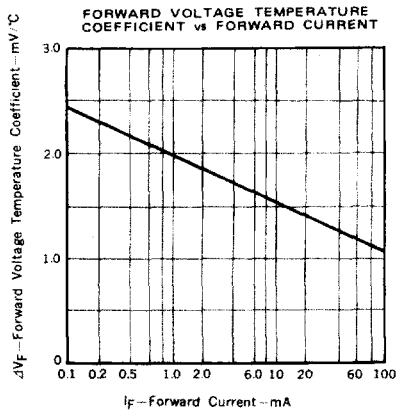
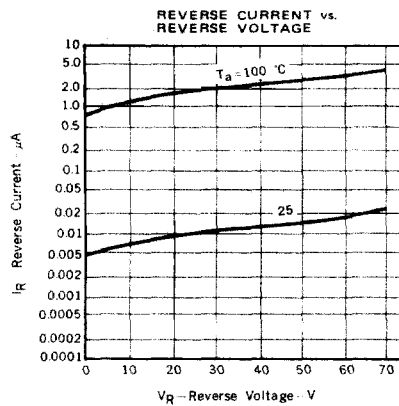
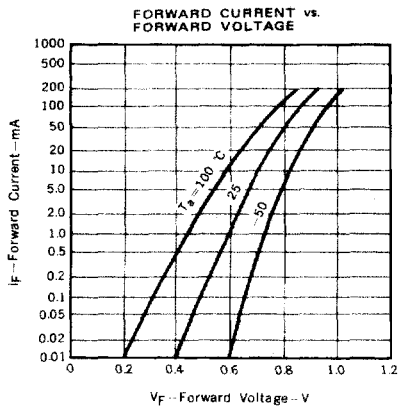
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Forward Voltage	V_{F1}		720	850	mV	$I_F = 10$ mA
	V_{F2}		850	1000	mV	$I_F = 50$ mA
	V_{F3}		950	1200	mV	$I_F = 100$ mA
Reverse Current	I_R	1SS222		1.0	μA	$V_R = 70$ V
		1SS223		1.0	μA	$V_R = 100$ V
Capacitance	C_t		2.0	4.0	pF	$V_R = 0$, $f = 1.0$ MHz
Reverse Recovery Time	t_{rr}			3.0	ns	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, See Test Circuit.

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NEC Corporation

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TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

SWITCHING CHARACTERISTICS TEST CIRCUIT

Reverse recovery time : t_{rr}

